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2335	Toward Defect-Free Doping by Self-Assembled Molecular Monolayers: The Evolution of Interstitial Carbon-Related Defects in Phosphorus-Doped Silicon.		
2334	Manganese Doping Stabilizes Perovskite Light-Emitting Diodes by Reducing Ion Migration.		
2333	New method to determine the photoionization threshold energy of a deep level from photocapacitance. 1974 , 25, 572-574		16
2332	Non-radiative recombination centers in GaAs _{0.6} P _{0.4} red light-emitting diodes. 1975 , 18, 635-640		15
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2330	Growth and characterization of GaP and GaAs _{1-x} P _x . 1975 , 31, 165-171		22
2329	A study of electron traps in vapour-phase epitaxial GaAs. 1975 , 8, 15-21		86
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